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# SILICON CARBIDE SINGLE PHASE FULL WAVE BRIDGE

**DESCRIPTION:** A 1200-VOLT, 10 AMP POWER SILICON CARBIDE SINGLE PHASE FULL WAVE BRIDGE IN A HERMETIC 5-PIN TO-258 (MO-078) PACKAGE

#### FEATURES:

- NO RECOVERY TIME OR REVERSE RECOVERY LOSSES
- NO TEMPERATURE INFLUENCE ON SWITCHING BEHAVIOR

**MAXIMUM RATINGS** ALL RATINGS ARE @ T<sub>C</sub> = 25 °C UNLESS OTHERWISE SPECIFIED. RATING SYMBOL UNITS MAX. PEAK INVERSE VOLTAGE PIV 1200 Volts MAXIMUM DC OUTPUT CURRENT PER LEG 10  $|_0$ Amps MAXIMUM REPETITIVE FORWARD SURGE CURRENT PER LEG 50 Amps I<sub>FRM</sub> (t = 8.3 ms, Sine)MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT PER LEG 250 Amps I<sub>FSM</sub>  $(t = 10\mu s, pulse)$ 70 MAXIMUM JUNCTION CAPACITANCE PER LEG (Vr = 400V) Ст pF MAXIMUM POWER DISSIPATION  $P_d$ 80 W MAXIMUM THERMAL RESISTANCE (Junction to Case) 0.50 °C/W R<sub>0JC</sub> MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE Top, Tstg -55 to °C +200

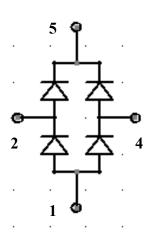
## **ELECTRICAL CHARACTERISTICS**

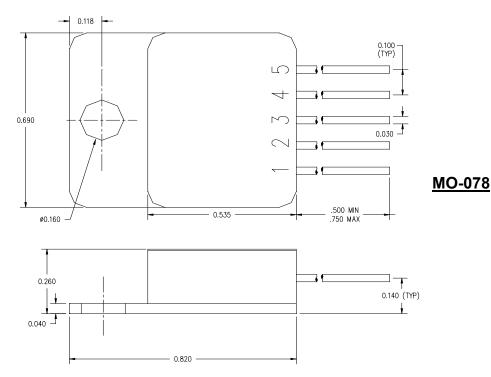
CHARACTERISTIC	TYP	MAX.	UNITS
MAXIMUM FORWARD VOLTAGE DROP I <sub>f</sub> =10A PER LEG, T <sub>J</sub> =25 °C	1.60	1.80	
T_J=175 °C	2.50	3.00	Volts
MAXIMUM REVERSE CURRENT PIV = 1200V PER LEG, $T_J$ = 25 °C	0.01	0.20	
T <sub>J</sub> = 175 °C	0.02	1.00	mA
TOTAL CAPACITIVE CHARGE PER LEG (V <sub>R</sub> =1200V, I <sub>F</sub> =10A, di/dt=500A/µs and T <sub>J</sub> =25°C) $Q_C$	60	N/A	nC

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#### **PINOUT TABLE**

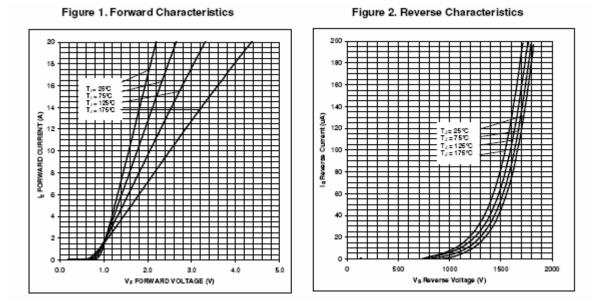
DEVICE TYPE	PIN 1	PIN 2	PIN 3	PIN 4	PIN 5
SINGLE PHASE FULL WAVE BRIDGE	DC(-)	AC(1)	NC	AC(2)	DC(+)

Application Note: Customers should be aware that at the current stage of technical development of SiC, the reverse avalanche capabilities of the device are limited.

Customer designs will need to accommodate these limitations and avoid exposure of the device to this and other potentially damaging conditions in their applications.

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Forward and Reverse Characteristics for Individual Diode



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